

Input low voltage

Input high voltage

Output low voltage

Output high voltage

Clock input low voltage

Clock input high voltage

Clock output low voltage

Clock output high voltage

Input leakage

Clock input leakage

Silence voltage

Peak to peak speech output

External load on speech output

30	ZERO
31	A
32	B
33	C
34	D
35	E
36	F
37	G
38	H
39	I
40	J
41	K
42	L
43	M
44	N

$t_{WSS}$

$t_F$

$t_{SU}$

$t_W$

$t_H$

Table 3 A.C. switch  
ROMS

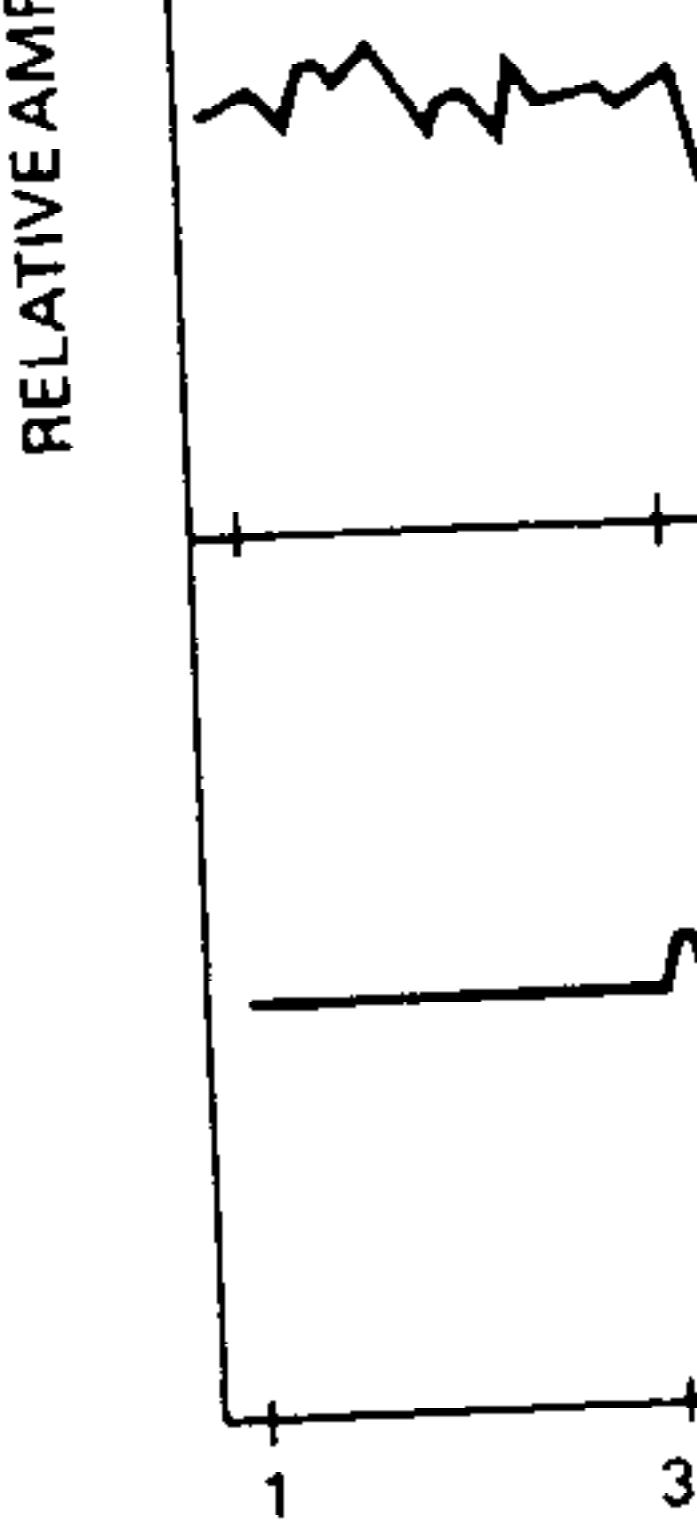
Parameter
Chip select access time
Output turn off delay
Address access time
Input capacitance $C_I$
Output capacitance

**WR** Write strobe

The write strobe line latches (SW1-SW8) into an internal edge of WR the speech pro of the command specified by sequence is shown in the t 1. If a command to start a n issued during a speech seq will be started immediately to a switch it must be a si type.

**R** data 1-8 ROM data

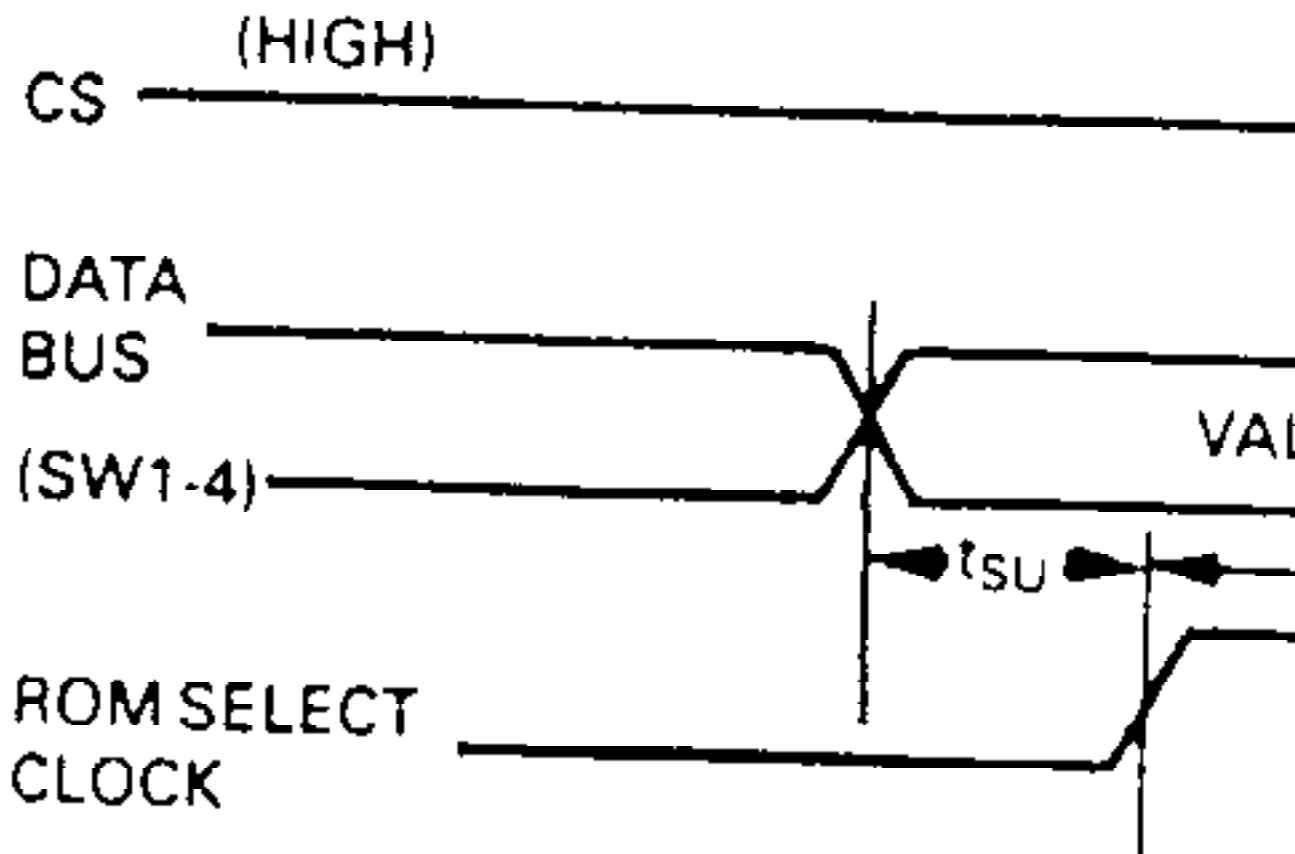
This is the 8-bit parallel data speech data from the speech



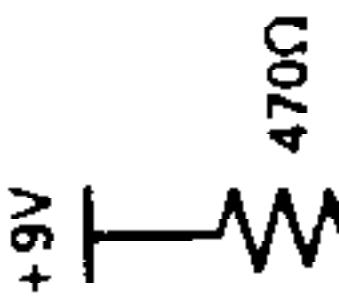
- (a) Original Speed
- (b) Phase Angle
- (c) Half-Period Z

A high on SW4 line during the audio output to be muted

Figure 5 ROM Select sequence



**Figure 6 Speech synthesis circuit**



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